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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74LVC16240A

16-bit Buffers / Line Drivers with 3-state Outputs

ADE-205-118B(Z)

3rd Edition
December 1996

Description

The HD74LVC16240A has sixteen inverter drivers with three state outputs in a 48 pin package. This device is a inverting buffer and has two active low enables ($1\overline{G}$ to $4\overline{G}$). Each enable independently controls four buffers. Low voltage and high speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

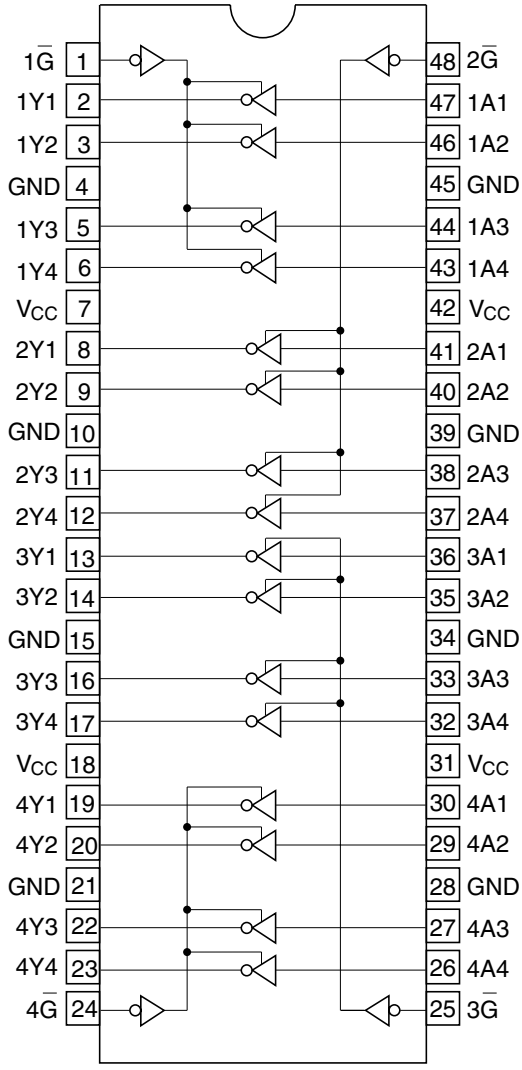
- V_{CC} = 2.0 V to 5.5 V
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V)
- All outputs V_{OUT} (Max.) = 5.5 V (@V_{CC} = 0 V or output off state)
- Typical V_{OL} ground bounce < 0.8 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@V_{CC} = 3.3 V, Ta = 25°C)
- High output current ±24 mA (@V_{CC} = 3.0 V to 5.5 V)

Function Table

Inputs		
$\overline{G}$	A	Output Y
H	X	Z
L	H	L
L	L	H

H: High level
L: Low level
X: Immaterial
Z: High impedance

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	–0.5 to 6.0	V	
Input diode current	I_{IK}	–50	mA	V_I = –0.5 V
Input voltage	V_I	–0.5 to 6.0	V	
Output diode current	I_{OK}	–50	mA	V_O = –0.5 V
		50	mA	V_O = V_{CC} +0.5 V
Output voltage	V_O	–0.5 to V_{CC} +0.5	V	Output “H” or “L”
		–0.5 to 6.0	V	Output “Z” or V_{CC}:OFF
Output current	I_O	±50	mA	
V_{CC}, GND current / pin	I_{CC} or I_{GND}	100	mA	
Storage temperature	Tstg	–65 to +150	°C	

Note: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Rating	Unit	Conditions
Supply voltage	V_{CC}	1.5 to 5.5	V	Data hold
		2.0 to 5.5	V	At operation
Input / output voltage	V_I	0 to 5.5	V	$\overline{G}$, A
	V_O	0 to V_{CC}	V	Output "H" or "L"
		0 to 5.5	V	Output "Z" or V_{CC}:OFF
Operating temperature	Ta	–40 to 85	°C	
Output current	I_{OH}	–12	mA	V_{CC} = 2.7 V
		–24[*2]	mA	V_{CC} = 3.0 V to 5.5 V
	I_{OL}	12	mA	V_{CC} = 2.7 V
		24[*2]	mA	V_{CC} = 3.0 V to 5.5 V
Input rise / fall time [*1]	t_r, t_f	10	ns/V	

Notes: 1. This item guarantees maximum limit when one input switches.
Waveform : Refer to test circuit of switching characteristics.
2. duty cycle ≤ 50%

Electrical Characteristics

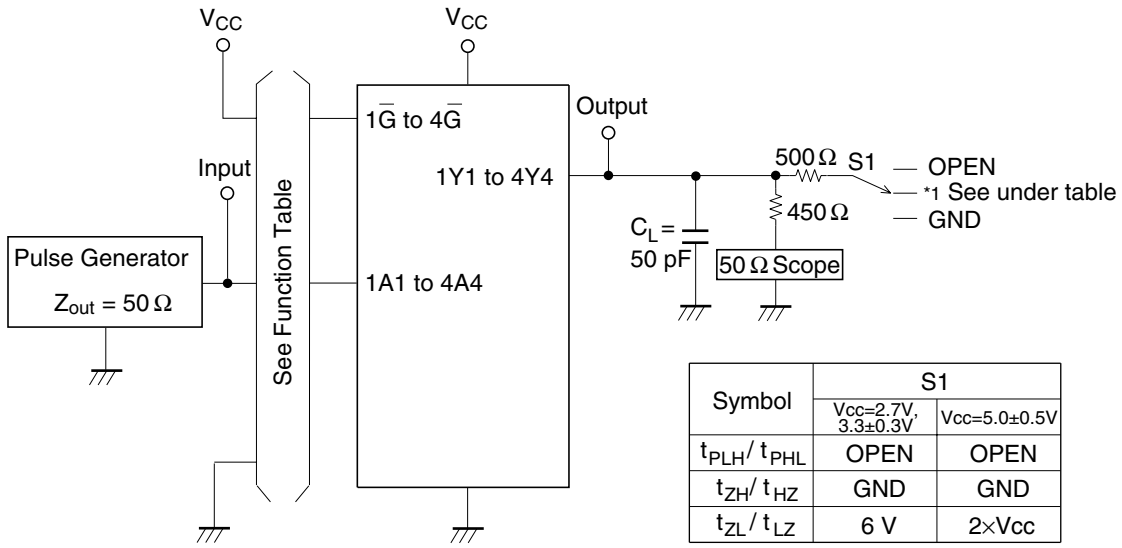
			Ta = –40 to 85°C			
Item	**Symbol**	**V_{CC} (V)**	**Min**	**Max**	**Unit**	**Test Conditions**
Input voltage	V_{IH}	2.7 to 3.6	2.0	—	V	
		4.5 to 5.5	V_{CC} ×0.7	—	V	
	V_{IL}	2.7 to 3.6	—	0.8	V	
		4.5 to 5.5	—	V_{CC}×0.3	V	
Output voltage	V_{OH}	2.7 to 5.5	V_{CC} –0.2	—	V	I_{OH} = –100 µA
		2.7	2.2	—	V	I_{OH} = –12 mA
		3.0	2.4	—	V	
		3.0	2.2	—	V	I_{OH} = –24 mA
		4.5	3.8	—	V	
	V_{OL}	2.7 to 5.5	—	0.2	V	I_{OL} = 100 µA
		2.7	—	0.4	V	I_{OL} = 12 mA
		3.0	—	0.55	V	I_{OL} = 24 mA
		4.5	—	0.55	V	
Input current	I_{IN}	0 to 5.5	—	±5.0	µA	V_{IN} = 5.5 V or GND
Off state output current	I_{OZ}	2.7 to 5.5	—	±5.0	µA	V_{IN} = V_{CC}, GND V_{OUT} = 5.5 V or GND
Output leak current	I_{OFF}	0	—	20	µA	V_{IN} / V_{OUT} = 5.5 V
Quiescent supply current	I_{CC}	2.7 to 3.6	—	±20	µA	V_{IN} / V_{OUT} = 3.6 to 5.5 V
		2.7 to 5.5	—	20	µA	V_{IN} = V_{CC} or GND
	ΔI_{CC}	3.0 to 3.6	—	500	µA	V_{IN} = one input at(V_{CC} –0.6)V, other inputs at V_{CC} or GND

Switching Characteristics

			Ta = –40 to 85°C					
Item	**Symbol**	**V_{cc} (V)**	**Min**	**Typ**	**Max**	**Unit**	**From (Input)**	**To (Output)**
Propagation delay time	t_{PLH}	2.7	—	—	6.2	ns	A	Y
	t_{PHL}	3.3±0.3	1.5	—	5.5	ns		
		5.0±0.5	—	—	4.5	ns		
Output enable time	t_{ZH}	2.7	—	—	7.7	ns	$\overline{G}$	Y
	t_{ZL}	3.3±0.3	1.5	—	7.0	ns		
		5.0±0.5	—	—	6.0	ns		
Output disable time	t_{HZ}	2.7	—	—	7.7	ns	$\overline{G}$	Y
	t_{LZ}	3.3±0.3	1.5	—	7.0	ns		
		5.0±0.5	—	—	6.0	ns		
Between output pins skew [*1]	t_{OSLH}	2.7	—	—	—	ns		
	t_{OSHL}	3.3±0.3	—	—	1.0	ns		
		5.0±0.5	—	—	1.0	ns		
Input capacitance	C_{IN}	2.7	—	3.0	—	pF		
Output capacitance	C_O	2.7	—	15.0	—	pF		

Note: 1. This parameter is characterized but not tested.
$tos_{LH} = | t_{PLHm} - t_{PLHn} |$, $tos_{HL} = | t_{PHLm} - t_{PHLn} |$

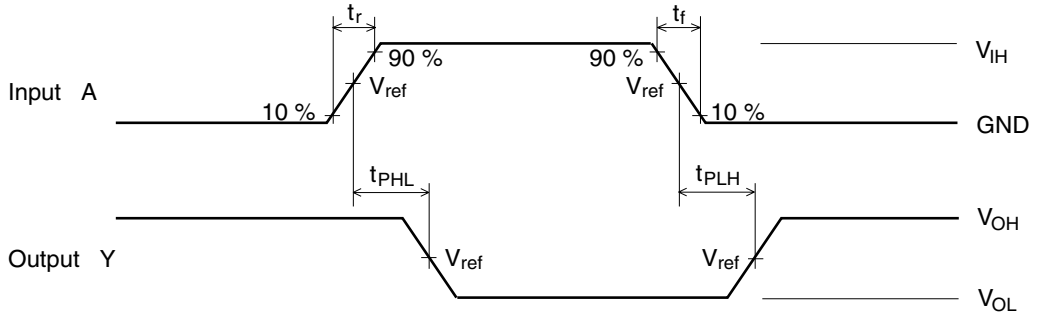
Test Circuit



Symbol	S1	
	Vcc=2.7V, 3.3±0.3V	Vcc=5.0±0.5V
t_{PLH}/ t_{PHL}	OPEN	OPEN
t_{ZH}/ t_{HZ}	GND	GND
t_{ZL}/ t_{LZ}	6 V	2×Vcc

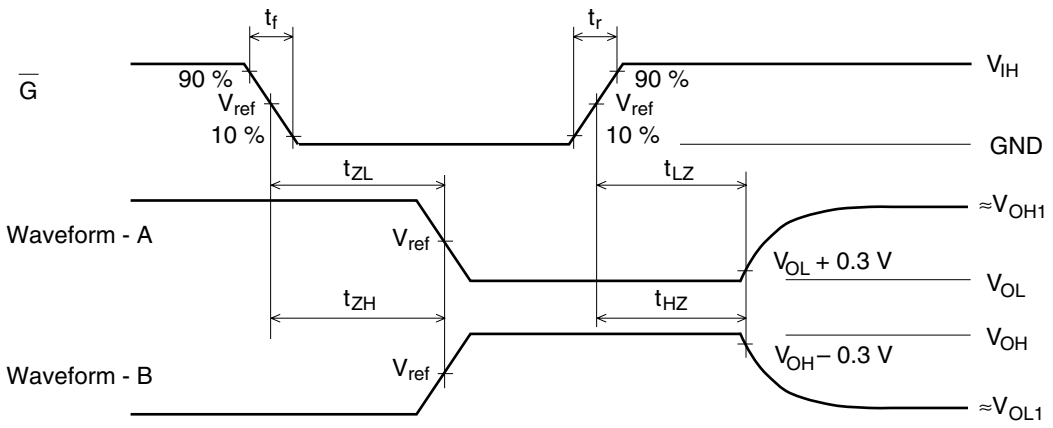
Note: 1. C_L includes probe and jig capacitance.

Waveforms – 1



Notes: 1. t_r = 2.5 ns, t_f = 2.5 ns
2. Input waveform : PRR = 10 MHz, duty cycle 50%

Waveforms – 2



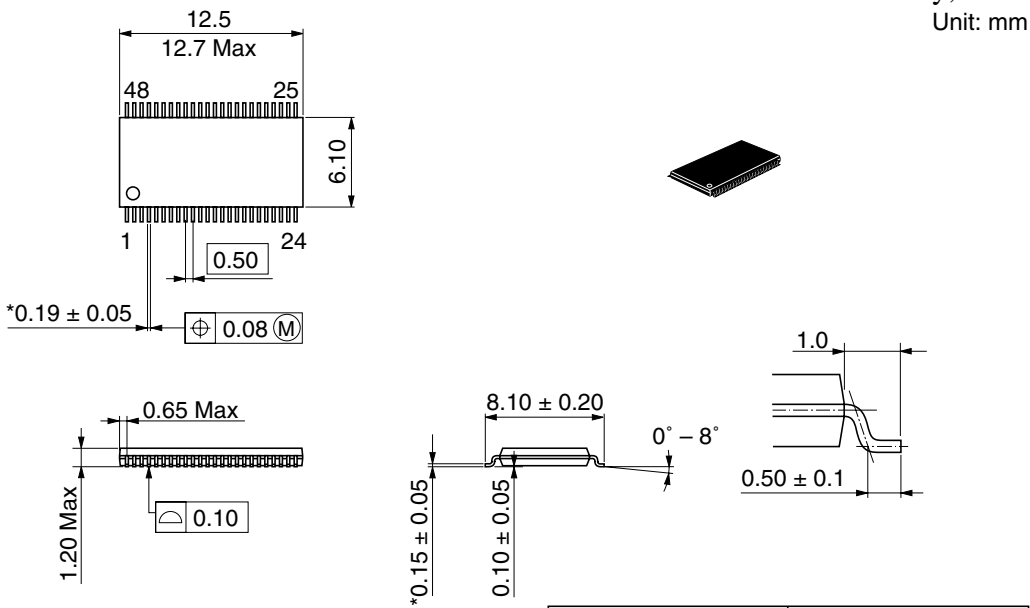
TEST	Vcc=2.7V, 3.3±0.3V	Vcc=5.0±0.5V
V_{IH}	2.7 V	Vcc
V_{ref}	1.5 V	50%Vcc
V_{OH1}	3 V	Vcc
V_{OL1}	GND	GND

Notes:
1. t_r = 2.5 ns, t_f = 2.5 ns
2. Input waveform : PRR = 10 MHz, duty cycle 50%
3. Waveform – A shows input conditions such that the output is "L" level when enable by the output control.
4. Waveform – B shows input conditions such that the output is "H" level when enable by the output control.

Package Dimensions

As of July, 2001

Unit: mm



Hitachi Code	TTP-48DBV
JEDEC	—
JEITA	—
Mass (reference value)	0.20 g

*Pd plating

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